

### **PN3563**



## **NPN RF Amplifier**

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	15	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	2.0	V
I <sub>C</sub>	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN3563	
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

<sup>1)</sup> These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## NPN RF Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
055.014	DAOTEDIOTIOO				
	RACTERISTICS	I 20 m	15	1	V
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage*	$I_C = 3.0 \text{ mA}, I_B = 0$			•
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100  \mu A, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10  \mu A,  I_C = 0$	2.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, I_{E} = 0$ $V_{CB} = 15 \text{ V}, T_{A} = 150^{\circ}\text{C}$		0.05 5.0	μA nA
ON CHAR	RACTERISTICS*				
ON CHAF	RACTERISTICS*				
	RACTERISTICS*  DC Current Gain	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V}$	20	200	
h <sub>FE</sub>		$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V}$	20	200	
h <sub>FE</sub>	DC Current Gain	$I_{C}$ = 8.0 mA, $V_{CE}$ = 10 V $I_{C}$ = 8.0 mA, $V_{CE}$ = 10 V, $f$ = 100 MHz	20	200	MHz
h <sub>FE</sub>	DC Current Gain  IGNAL CHARACTERISTICS	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$	-		MHz pF pF
h <sub>FE</sub> SMALL S  f <sub>T</sub>	DC Current Gain  IGNAL CHARACTERISTICS  Current Gain - Bandwidth Product	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$	-	1500	pF
SMALL S f <sub>T</sub> Cobo	DC Current Gain  IGNAL CHARACTERISTICS  Current Gain - Bandwidth Product  Output Capacitance	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$ $V_{CB} = 0, I_{E} = 0, f = 1.0 \text{ MHz}$	-	1500 1.7 3.0	pF pF

 $I_C = 8.0 \text{ mA}, V_{CB} = 10 \text{ V},$ f = 200 MHz

14

26

dΒ

 $\mathsf{G}_{\mathsf{pe}}$ 

Amplifier Power Gain

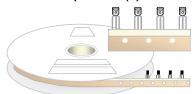
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z 2,000 D75Z **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

### TO-92 Tape and Reel Data, continued

### **TO-92 Reeling Style** Configuration: Figure 2.0

### Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM

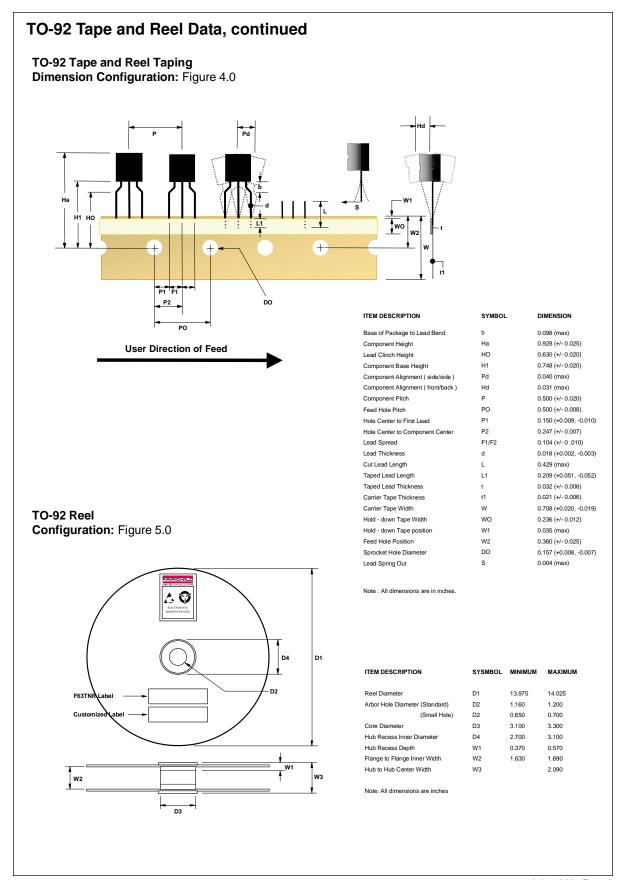
# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

### **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0





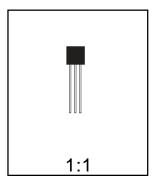


### **TO-92 Package Dimensions**



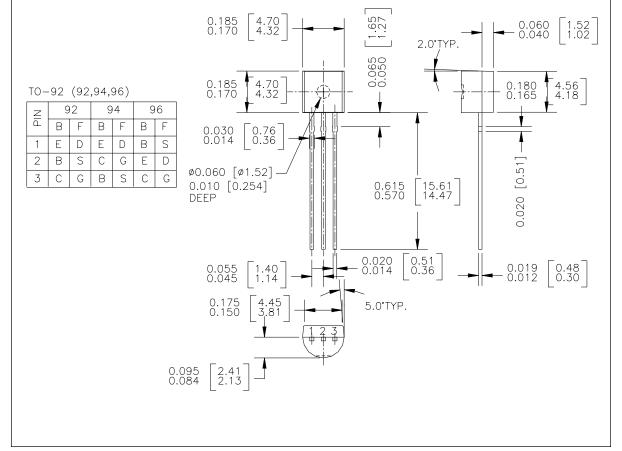
## TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

 $ACEx^{TM}$  $FASTr^{TM}$ PowerTrench® SyncFET<sup>TM</sup> QFET™ TinyLogic™ Bottomless™ GlobalOptoisolator™ QS<sup>TM</sup> UHC™ CoolFET™ GTO™ QT Optoelectronics™ **VCXTM** CROSSVOLT™ HiSeC™

DOME™ ISOPLANAR™ Quiet Series™
E²CMOS™ MICROWIRF™ SILENT SWITC

### **DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### PRODUCT STATUS DEFINITIONS

### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.